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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Obsolete
Core Processor	R8C
Core Size	16-Bit
Speed	20MHz
Connectivity	I²C, SIO, SSU, UART/USART
Peripherals	LED, POR, Voltage Detect, WDT
Number of I/O	13
Program Memory Size	16KB (16K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	1K x 8
Voltage - Supply (Vcc/Vdd)	2.7V ~ 5.5V
Data Converters	A/D 4x10b
Oscillator Type	Internal
Operating Temperature	-20°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	28-WFQFN Exposed Pad
Supplier Device Package	28-HWQFN (5x5)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f211a4np-u0

Table 1.2 Functions and Specifications for R8C/1B Group

Item		Specification
CPU	Number of fundamental instructions	89 instructions
	Minimum instruction execution time	50 ns (f(XIN) = 20 MHz, VCC = 3.0 to 5.5 V) 100 ns (f(XIN) = 10 MHz, VCC = 2.7 to 5.5 V)
	Operating mode	Single-chip
	Address space	1 Mbyte
	Memory capacity	See **Table 1.4 Product Information for R8C/1B Group**
Peripheral Functions	Ports	I/O ports: 13 pins (including LED drive port) Input port: 3 pins
	LED drive ports	I/O ports: 4 pins
	Timers	Timer X: 8 bits × 1 channel, timer Z: 8 bits × 1 channel (Each timer equipped with 8-bit prescaler) Timer C: 16 bits × 1 channel (Input capture and output compare circuits)
	Serial interfaces	1 channel Clock synchronous serial I/O, UART 1 channel UART
	Clock synchronous serial interface	1 channel I²C bus Interface(1) Clock synchronous serial I/O with chip select (SSU)
	A/D converter	10-bit A/D converter: 1 circuit, 4 channels
	Watchdog timer	15 bits × 1 channel (with prescaler) Reset start selectable, count source protection mode
	Interrupts	Internal: 11 sources, External: 4 sources, Software: 4 sources, Priority levels: 7 levels
	Clock generation circuits	2 circuits • Main clock generation circuit (with on-chip feedback resistor) • On-chip oscillator (high speed, low speed) High-speed on-chip oscillator has a frequency adjustment function
	Oscillation stop detection function	Main clock oscillation stop detection function
	Voltage detection circuit	On-chip
	Power on reset circuit	On-chip
Electric Characteristics	Supply voltage	VCC = 3.0 to 5.5 V (f(XIN) = 20 MHz) VCC = 2.7 to 5.5 V (f(XIN) = 10 MHz)
	Current consumption	Typ. 9 mA (VCC = 5.0 V, f(XIN) = 20 MHz, A/D converter stopped) Typ. 5 mA (VCC = 3.0 V, f(XIN) = 10 MHz, A/D converter stopped) Typ. 35 μA (VCC = 3.0 V, wait mode, peripheral clock off) Typ. 0.7 μA (VCC = 3.0 V, stop mode)
Flash Memory	Programming and erasure voltage	VCC = 2.7 to 5.5 V
	Programming and erasure endurance	10,000 times (data flash) 1,000 times (program ROM)
Operating Ambient Temperature		-20 to 85°C -40 to 85°C (D version) -20 to 105°C (Y version) (2)
Package		20-pin molded-plastic LSSOP 20-pin molded-plastic SDIP 28-pin molded-plastic HWQFN

NOTE:
1. I²C bus is a trademark of Koninklijke Philips Electronics N. V.
2. Please contact Renesas Technology sales offices for the Y version.

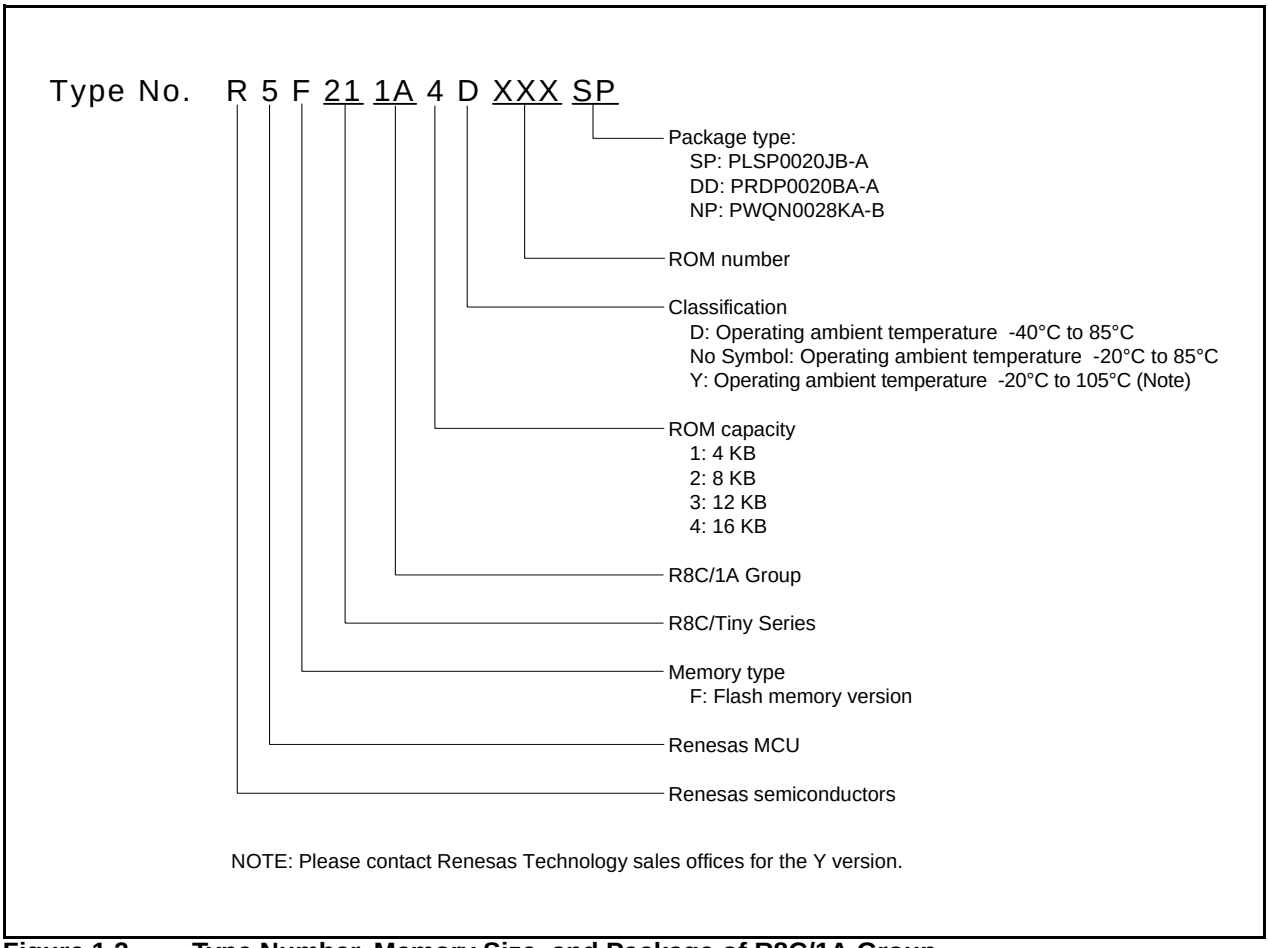


Figure 1.2 Type Number, Memory Size, and Package of R8C/1A Group

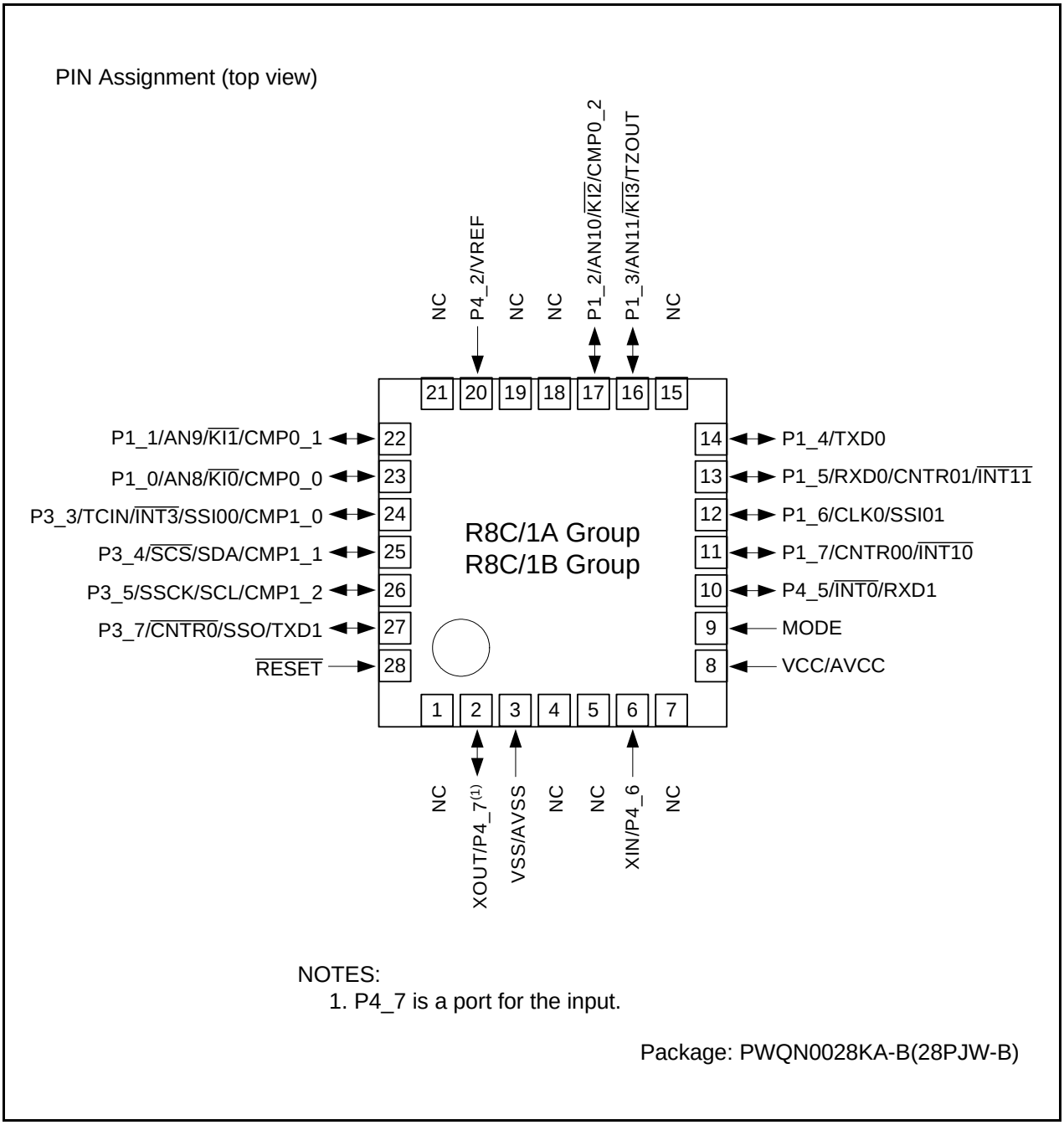


Figure 1.6 Pin Assignments for PWQN0028KA-B Package (Top View)

1.6 Pin Functions

Table 1.5 lists Pin Functions, Table 1.6 lists Pin Name Information by Pin Number of PLSP0020JB-A, PRDP0020BA-A Packages and Table 1.7 lists Pin Name Information by Pin Number of PWQN0028KA-B Package.

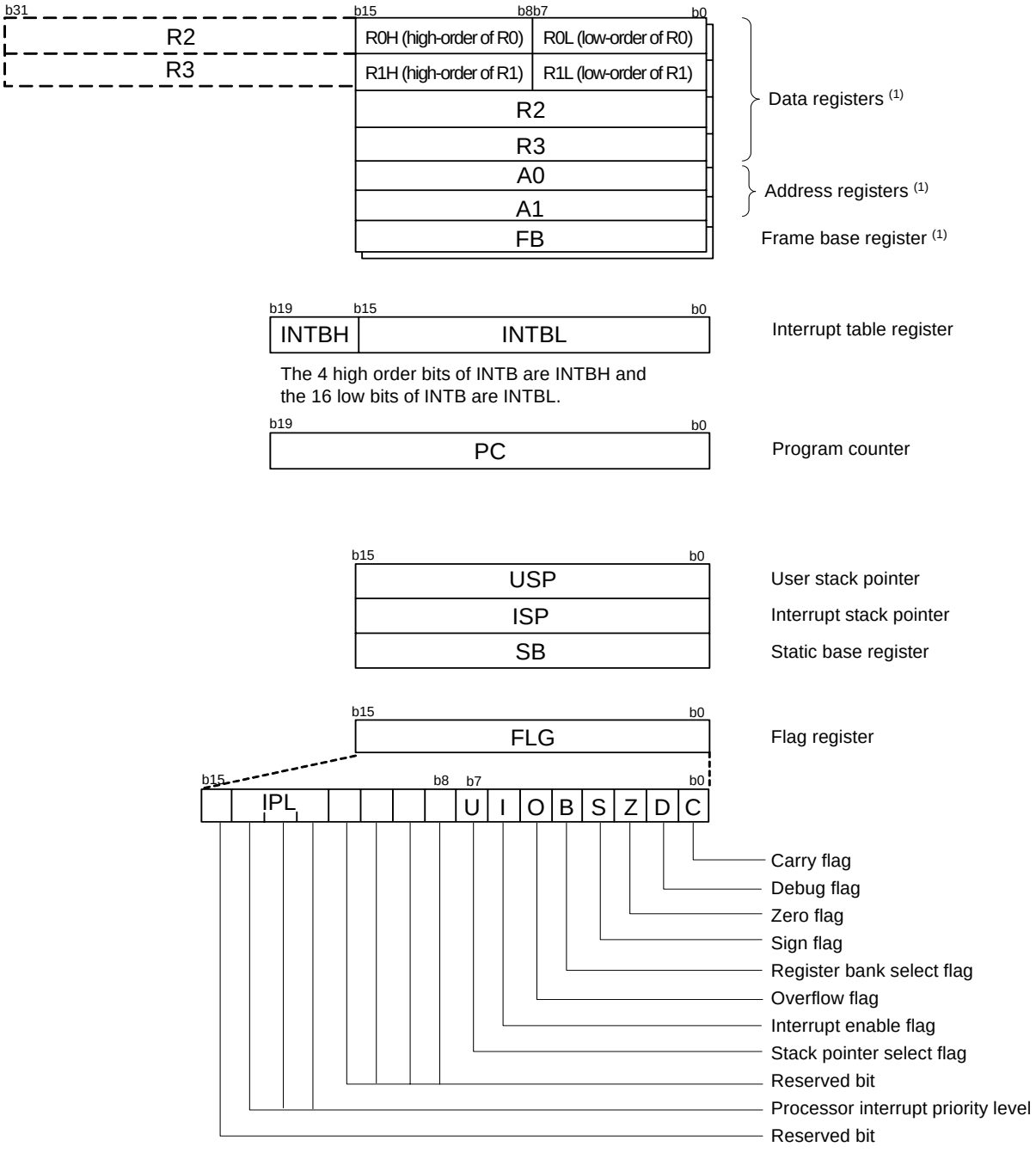
Table 1.5 Pin Functions

Type	Symbol	I/O Type	Description
Power Supply Input	VCC, VSS	I	Apply 2.7 V to 5.5 V to the VCC pin. Apply 0 V to the VSS pin.
Analog Power Supply Input	AVCC, AVSS	I	Power supply for the A/D converter Connect a capacitor between AVCC and AVSS.
Reset Input	$\overline{\text{RESET}}$	I	Input “L” on this pin resets the MCU.
MODE	MODE	I	Connect this pin to VCC via a resistor.
Main Clock Input	XIN	I	These pins are provided for main clock generation circuit I/O. Connect a ceramic resonator or a crystal oscillator between the XIN and XOUT pins. To use an external clock, input it to the XIN pin and leave the XOUT pin open.
Main Clock Output	XOUT	O	
$\overline{\text{INT}}$ Interrupt	$\overline{\text{INT0}}$, $\overline{\text{INT1}}$, $\overline{\text{INT3}}$	I	INT interrupt input pins
Key Input Interrupt	$\overline{\text{KI0}}$ to $\overline{\text{KI3}}$	I	Key input interrupt input pins
Timer X	CNTR0	I/O	Timer X I/O pin
	$\overline{\text{CNTR0}}$	O	Timer X output pin
Timer Z	TZOUT	O	Timer Z output pin
Timer C	TCIN	I	Timer C input pin
	CMP0_0 to CMP0_2, CMP1_0 to CMP1_2	O	Timer C output pins
Serial Interface	CLK0	I/O	Transfer clock I/O pin
	RXD0, RXD1	I	Serial data input pins
	TXD0, TXD1	O	Serial data output pins
Clock synchronous serial I/O with chip select (SSU)	SSI00, SSI01	I/O	Data I/O pin.
	$\overline{\text{SCS}}$	I/O	Chip-select signal I/O pin
	SSCK	I/O	Clock I/O pin
	SSO	I/O	Data I/O pin
I^2C bus Interface	SCL	I/O	Clock I/O pin
	SDA	I/O	Data I/O pin
Reference Voltage Input	VREF	I	Reference voltage input pin to A/D converter
A/D Converter	AN8 to AN11	I	Analog input pins to A/D converter
I/O Port	P1_0 to P1_7, P3_3 to P3_5, P3_7, P4_5	I/O	CMOS I/O ports. Each port has an I/O select direction register, allowing each pin in the port to be directed for input or output individually. Any port set to input can be set to use a pull-up resistor or not by a program. P1_0 to P1_3 also function as LED drive ports.
Input Port	P4_2, P4_6, P4_7	I	Input-only ports

I: Input O: Output I/O: Input and output

2. Central Processing Unit (CPU)

Figure 2.1 shows the CPU Registers. The CPU contains 13 registers. R0, R1, R2, R3, A0, A1, and FB configure a register bank. There are two sets of register bank.



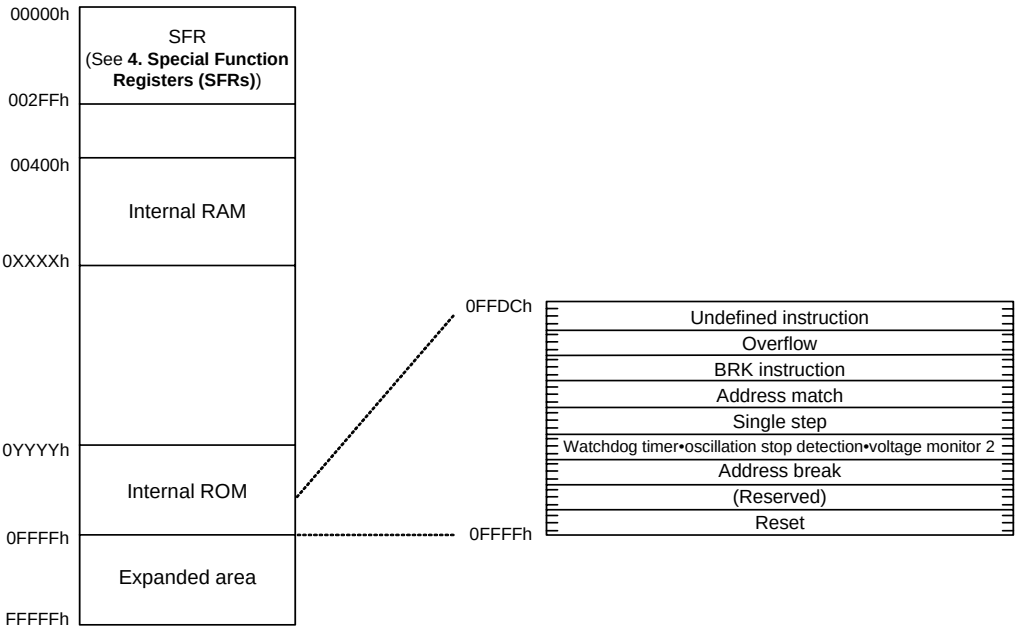
NOTE:
1. These registers comprise a register bank. There are two register banks.

Figure 2.1 CPU Register

3. Memory

3.1 R8C/1A Group

Figure 3.1 is a Memory Map of R8C/1A Group. The R8C/1A Group has 1 Mbyte of address space from addresses 00000h to FFFFFh.
The internal ROM is allocated lower addresses, beginning with address 0FFFFh. For example, a 16-Kbyte internal ROM area is allocated addresses 0C000h to 0FFFFh.
The fixed interrupt vector table is allocated addresses 0FFDCh to 0FFFFh. They store the starting address of each interrupt routine.
The internal RAM is allocated higher addresses, beginning with address 00400h. For example, a 1-Kbyte internal RAM area is allocated addresses 00400h to 007FFh. The internal RAM is used not only for storing data but also for calling subroutines and as stacks when interrupt requests are acknowledged.
Special function registers (SFRs) are allocated addresses 00000h to 002FFh. The peripheral function control registers are allocated here. All addresses within the SFR, which have nothing allocated are reserved for future use and cannot be accessed by users.



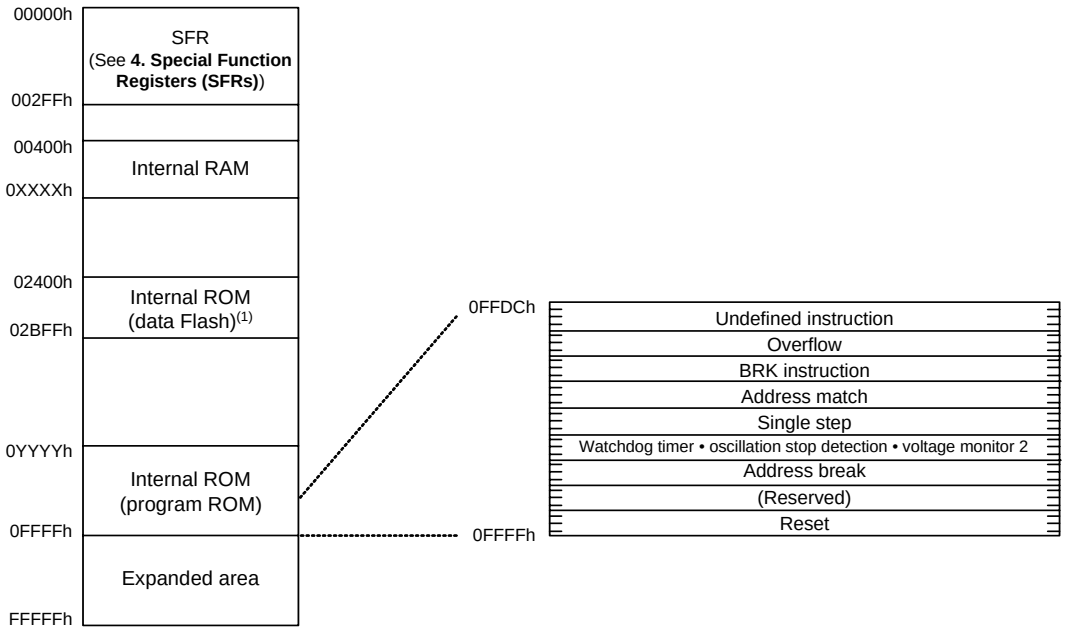
NOTE:
1. The blank regions are reserved. Do not access locations in these regions.

Part Number	Internal ROM		Internal RAM	
	Size	Address 0YYYYh	Size	Address 0XXXXh
R5F211A4SP, R5F211A4DSP, R5F211A4DD, R5F211A4NP, R5F211A4XXXSP, R5F211A4DXXXSP, R5F211A4XXXDD, R5F211A4XXXNP	16 Kbytes	0C000h	1 Kbyte	007FFh
R5F211A3SP, R5F211A3DSP, R5F211A3DD, R5F211A3NP, R5F211A3XXXSP, R5F211A3DXXXSP, R5F211A3XXXDD, R5F211A3XXXNP	12 Kbytes	0D000h	768 bytes	006FFh
R5F211A2SP, R5F211A2DSP, R5F211A2DD, R5F211A2NP, R5F211A2XXXSP, R5F211A2DXXXSP, R5F211A2XXXDD, R5F211A2XXXNP	8 Kbytes	0E000h	512 bytes	005FFh
R5F211A1SP, R5F211A1DSP, R5F211A1DD, R5F211A1XXXSP, R5F211A1DXXXSP, R5F211A1XXXDD	4 Kbytes	0F000h	384 bytes	0057Fh

Figure 3.1 Memory Map of R8C/1A Group

3.2 R8C/1B Group

Figure 3.2 is a Memory Map of R8C/1B Group. The R8C/1B Group has 1 Mbyte of address space from addresses 00000h to FFFFFh.
The internal ROM (program ROM) is allocated lower addresses, beginning with address 0FFFFh. For example, a 16-Kbyte internal ROM area is allocated addresses 0C000h to 0FFFFh.
The fixed interrupt vector table is allocated addresses 0FFDCh to 0FFFFh. They store the starting address of each interrupt routine.
The internal ROM (data flash) is allocated addresses 02400h to 02BFFh.
The internal RAM is allocated higher addresses beginning with address 00400h. For example, a 1-Kbyte internal RAM area is allocated addresses 00400h to 007FFh. The internal RAM is used not only for storing data but also for calling subroutines and as stacks when interrupt requests are acknowledged.
Special function registers (SFRs) are allocated addresses 00000h to 002FFh. The peripheral function control registers are allocated here. All addresses within the SFR, which have nothing allocated are reserved for future use and cannot be accessed by users.



NOTES:
1. Data flash block A (1 Kbyte) and B (1 Kbyte) are shown.
2. The blank regions are reserved. Do not access locations in these regions.

Part Number	Internal ROM		Internal RAM	
	Size	Address 0YYYYh	Size	Address 0XXXXh
R5F211B4SP, R5F211B4DSP, R5F211B4DD, R5F211B4NP, R5F211B4XXXSP, R5F211B4DXXXSP, R5F211B4XXXDD, R5F211B4XXXNP	16 Kbytes	0C000h	1 Kbyte	007FFh
R5F211B3SP, R5F211B3DSP, R5F211B3DD, R5F211B3NP, R5F211B3XXXSP, R5F211B3DXXXSP, R5F211B3XXXDD, R5F211B3XXXNP	12 Kbytes	0D000h	768 bytes	006FFh
R5F211B2SP, R5F211B2DSP, R5F211B2DD, R5F211B2NP, R5F211B2XXXSP, R5F211B2DXXXSP, R5F211B2XXXDD, R5F211B2XXXNP	8 Kbytes	0E000h	512 bytes	005FFh
R5F211B1SP, R5F211B1DSP, R5F211B1DD, R5F211B1XXXSP, R5F211B1DXXXSP, R5F211B1XXXDD	4 Kbytes	0F000h	384 bytes	0057Fh

Figure 3.2 Memory Map of R8C/1B Group

Table 4.4 SFR Information (4)(1)

Address	Register	Symbol	After reset
00C0h	A/D Register	AD	XXh
00C1h			XXh
00C2h			
00C3h			
00C4h			
00C5h			
00C6h			
00C7h			
00C8h			
00C9h			
00CAh			
00CBh			
00CCh			
00CDh			
00CEh			
00CFh			
00D0h			
00D1h			
00D2h			
00D3h			
00D4h	A/D Control Register 2	ADCON2	00h
00D5h			
00D6h	A/D Control Register 0	ADCON0	00000XXXb
00D7h	A/D Control Register 1	ADCON1	00h
00D8h			
00D9h			
00DAh			
00DBh			
00DCh			
00DDh			
00DEh			
00DFh			
00E0h			
00E1h	Port P1 Register	P1	XXh
00E2h			
00E3h	Port P1 Direction Register	PD1	00h
00E4h			
00E5h	Port P3 Register	P3	XXh
00E6h			
00E7h	Port P3 Direction Register	PD3	00h
00E8h	Port P4 Register	P4	XXh
00E9h			
00EAh	Port P4 Direction Register	PD4	00h
00EBh			
00ECh			
00EDh			
00EEh			
00EFh			
00F0h			
00F1h			
00F2h			
00F3h			
00F4h			
00F5h			
00F6h			
00F7h			
00F8h	Port Mode Register	PMR	00h
00F9h			
00FAh			
00FBh			
00FCh	Pull-Up Control Register 0	PUR0	00XX0000b
00FDh	Pull-Up Control Register 1	PUR1	XXXXXX0Xb
00FEh	Port P1 Drive Capacity Control Register	DRR	00h
00FFh	Timer C Output Control Register	TCOUT	00h
01B3h	Flash Memory Control Register 4	FMR4	01000000b
01B4h			
01B5h	Flash Memory Control Register 1	FMR1	1000000Xb
01B6h			
01B7h	Flash Memory Control Register 0	FMR0	00000001b
0FFFFh	Optional Function Select Register	OFS	(2)

X: Undefined

NOTES:

1. Blank regions, 0100h to 01B2h and 01B8h to 02FFh are all reserved. Do not access locations in these regions.
2. The OFS register cannot be changed by a user program. Use a flash programmer to write to it.

Table 5.4 Flash Memory (Program ROM) Electrical Characteristics

Symbol	Parameter	Conditions	Standard			Unit
			Min.	Typ.	Max.	
–	Program/erase endurance(2)	R8C/1A Group	100(3)	–	–	times
		R8C/1B Group	1,000(3)	–	–	times
–	Byte program time		–	50	400	µs
–	Block erase time		–	0.4	9	s
$t_{d(SR-SUS)}$	Time delay from suspend request until suspend		–	–	97+CPU clock × 6 cycles	µs
–	Interval from erase start/restart until following suspend request		650	–	–	µs
–	Interval from program start/restart until following suspend request		0	–	–	ns
–	Time from suspend until program/erase restart		–	–	3+CPU clock × 4 cycles	µs
–	Program, erase voltage		2.7	–	5.5	V
–	Read voltage		2.7	–	5.5	V
–	Program, erase temperature		0	–	60	°C
–	Data hold time(8)	Ambient temperature = 55 °C	20	–	–	year

NOTES:
1. V_{CC} = 2.7 to 5.5 V at T_{opr} = 0 to 60 °C, unless otherwise specified.
2. Definition of programming/erasure endurance
   The programming and erasure endurance is defined on a per-block basis.
   If the programming and erasure endurance is n (n = 100 or 10,000), each block can be erased n times. For example, if 1,024 1-byte writes are performed to block A, a 1 Kbyte block, and then the block is erased, the programming/erasure endurance still stands at one. However, the same address must not be programmed more than once per erase operation (overwriting prohibited).
3. Endurance to guarantee all electrical characteristics after program and erase. (1 to Min. value can be guaranteed).
4. If emergency processing is required, a suspend request can be generated independent of this characteristic. In that case the normal time delay to suspend can be applied to the request. However, we recommend that a suspend request with an interval of less than 650 µs is only used once because, if the suspend state continues, erasure cannot operate and the incidence of erasure error rises.
5. In a system that executes multiple programming operations, the actual erasure count can be reduced by writing to sequential addresses in turn so that as much of the block as possible is used up before performing an erase operation. For example, when programming groups of 16 bytes, the effective number of rewrites can be minimized by programming up to 128 groups before erasing them all in one operation. In addition, averaging the number of erase operations between block A and block B can further reduce the effective number of rewrites. It is also advisable to retain data on the erase count of each block and limit the number of erase operations to a certain number.
6. If an error occurs during block erase, attempt to execute the clear status register command, then execute the block erase command at least three times until the erase error does not occur.
7. Customers desiring programming/erasure failure rate information should contact their Renesas technical support representative.
8. The data hold time includes time that the power supply is off or the clock is not supplied.

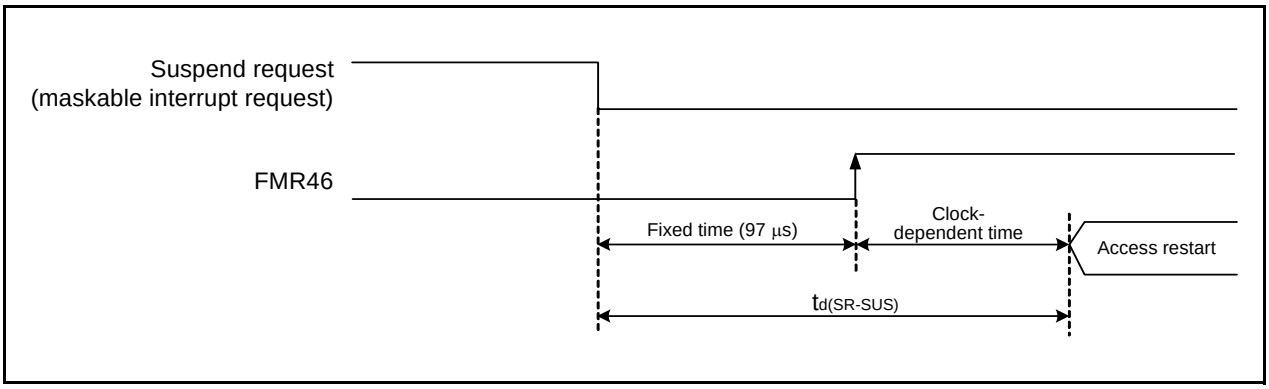


Figure 5.2 Transition Time to Suspend

Table 5.6 Voltage Detection 1 Circuit Electrical Characteristics

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
V_{det1}	Voltage detection level(3)		2.70	2.85	3.00	V
–	Voltage detection circuit self power consumption	VCA26 = 1, V_{CC} = 5.0 V	–	600	–	nA
$t_{d(E-A)}$	Waiting time until voltage detection circuit operation starts(2)		–	–	100	µs
Vccmin	MCU operating voltage minimum value		2.7	–	–	V

NOTES:
1. The measurement condition is V_{CC} = 2.7 V to 5.5 V and T_{opr} = -40°C to 85 °C.
2. Necessary time until the voltage detection circuit operates when setting to 1 again after setting the VCA26 bit in the VCA2 register to 0.
3. Ensure that $V_{det2} > V_{det1}$.

Table 5.7 Voltage Detection 2 Circuit Electrical Characteristics

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
V_{det2}	Voltage detection level(4)		3.00	3.30	3.60	V
–	Voltage monitor 2 interrupt request generation time(2)		–	40	–	µs
–	Voltage detection circuit self power consumption	VCA27 = 1, V_{CC} = 5.0 V	–	600	–	nA
$t_{d(E-A)}$	Waiting time until voltage detection circuit operation starts(3)		–	–	100	µs

NOTES:
1. The measurement condition is V_{CC} = 2.7 V to 5.5 V and T_{opr} = -40°C to 85 °C.
2. Time until the voltage monitor 2 interrupt request is generated after the voltage passes V_{det2}.
3. Necessary time until the voltage detection circuit operates when setting to 1 again after setting the VCA27 bit in the VCA2 register to 0.
4. Ensure that $V_{det2} > V_{det1}$.

Table 5.8 Reset Circuit Electrical Characteristics (When Using Voltage Monitor 1 Reset)

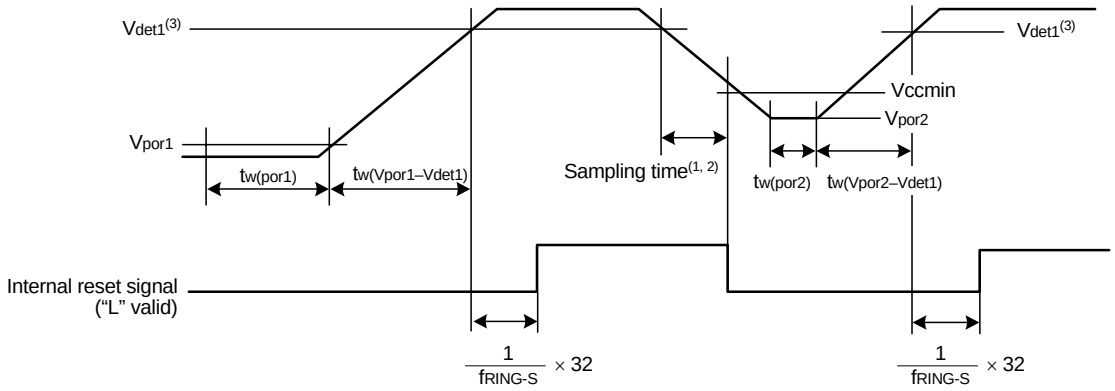
Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
V_{por2}	Power-on reset valid voltage	-20°C ≤ Topr ≤ 85°C	–	–	V_{det1}	V
$t_{w(Vpor2-Vdet1)}$	Supply voltage rising time when power-on reset is deasserted(1)	-20°C ≤ Topr ≤ 85°C, $t_{w(por2)}$ ≥ 0s(3)	–	–	100	ms

NOTES:
1. This condition is not applicable when using with Vcc ≥ 1.0 V.
2. When turning power on after the time to hold the external power below effective voltage (V_{por1}) exceeds10 s, refer to **Table 5.9 Reset Circuit Electrical Characteristics (When Not Using Voltage Monitor 1 Reset)**.
3. $t_{w(por2)}$ is the time to hold the external power below effective voltage (V_{por2}).

Table 5.9 Reset Circuit Electrical Characteristics (When Not Using Voltage Monitor 1 Reset)

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
V_{por1}	Power-on reset valid voltage	-20°C ≤ Topr ≤ 85°C	–	–	0.1	V
$t_{w(Vpor1-Vdet1)}$	Supply voltage rising time when power-on reset is deasserted	0°C ≤ Topr ≤ 85°C, $t_{w(por1)}$ ≥ 10 s(2)	–	–	100	ms
$t_{w(Vpor1-Vdet1)}$	Supply voltage rising time when power-on reset is deasserted	-20°C ≤ Topr < 0°C, $t_{w(por1)}$ ≥ 30 s(2)	–	–	100	ms
$t_{w(Vpor1-Vdet1)}$	Supply voltage rising time when power-on reset is deasserted	-20°C ≤ Topr < 0°C, $t_{w(por1)}$ ≥ 10 s(2)	–	–	1	ms
$t_{w(Vpor1-Vdet1)}$	Supply voltage rising time when power-on reset is deasserted	0°C ≤ Topr ≤ 85°C, $t_{w(por1)}$ ≥ 1 s(2)	–	–	0.5	ms

NOTES:
1. When not using voltage monitor 1, use with Vcc≥ 2.7 V.
2. $t_{w(por1)}$ is the time to hold the external power below effective voltage (V_{por1}).



NOTES:
1. Hold the voltage inside the MCU operation voltage range (Vccmin or above) within the sampling time.
2. The sampling clock can be selected. Refer to **7. Voltage Detection Circuit** for details.
3. V_{det1} indicates the voltage detection level of the voltage detection 1 circuit. Refer to **7. Voltage Detection Circuit** for details.

Figure 5.3 Reset Circuit Electrical Characteristics

Table 5.10 High-Speed On-Chip Oscillator Circuit Electrical Characteristics

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
–	High-speed on-chip oscillator frequency when the reset is deasserted	V_{CC} = 5.0 V, T_{opr} = 25 °C	–	8	–	MHz
–	High-speed on-chip oscillator frequency temperature • supply voltage dependence(2)	0 to +60 °C/5 V ± 5 %(3)	7.76	–	8.24	MHz
		-20 to +85 °C/2.7 to 5.5 V(3)	7.68	–	8.32	MHz
		-40 to +85 °C/2.7 to 5.5 V(3)	7.44	–	8.32	MHz

NOTES:
1. The measurement condition is V_{CC} = 5.0 V and T_{opr} = 25 °C.
2. Refer to **10.6.4 High-Speed On-Chip Oscillator Clock** for notes on high-speed on-chip oscillator clock.
3. The standard value shows when the HRA1 register is assumed as the value in shipping and the HRA2 register value is set to 00h.

Table 5.11 Power Supply Circuit Timing Characteristics

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
$t_{d(P-R)}$	Time for internal power supply stabilization during power-on(2)		1	–	2000	µs
$t_{d(R-S)}$	STOP exit time(3)		–	–	150	µs

NOTES:
1. The measurement condition is V_{CC} = 2.7 to 5.5 V and T_{opr} = 25 °C.
2. Waiting time until the internal power supply generation circuit stabilizes during power-on.
3. Time until CPU clock supply starts after the interrupt is acknowledged to exit stop mode.

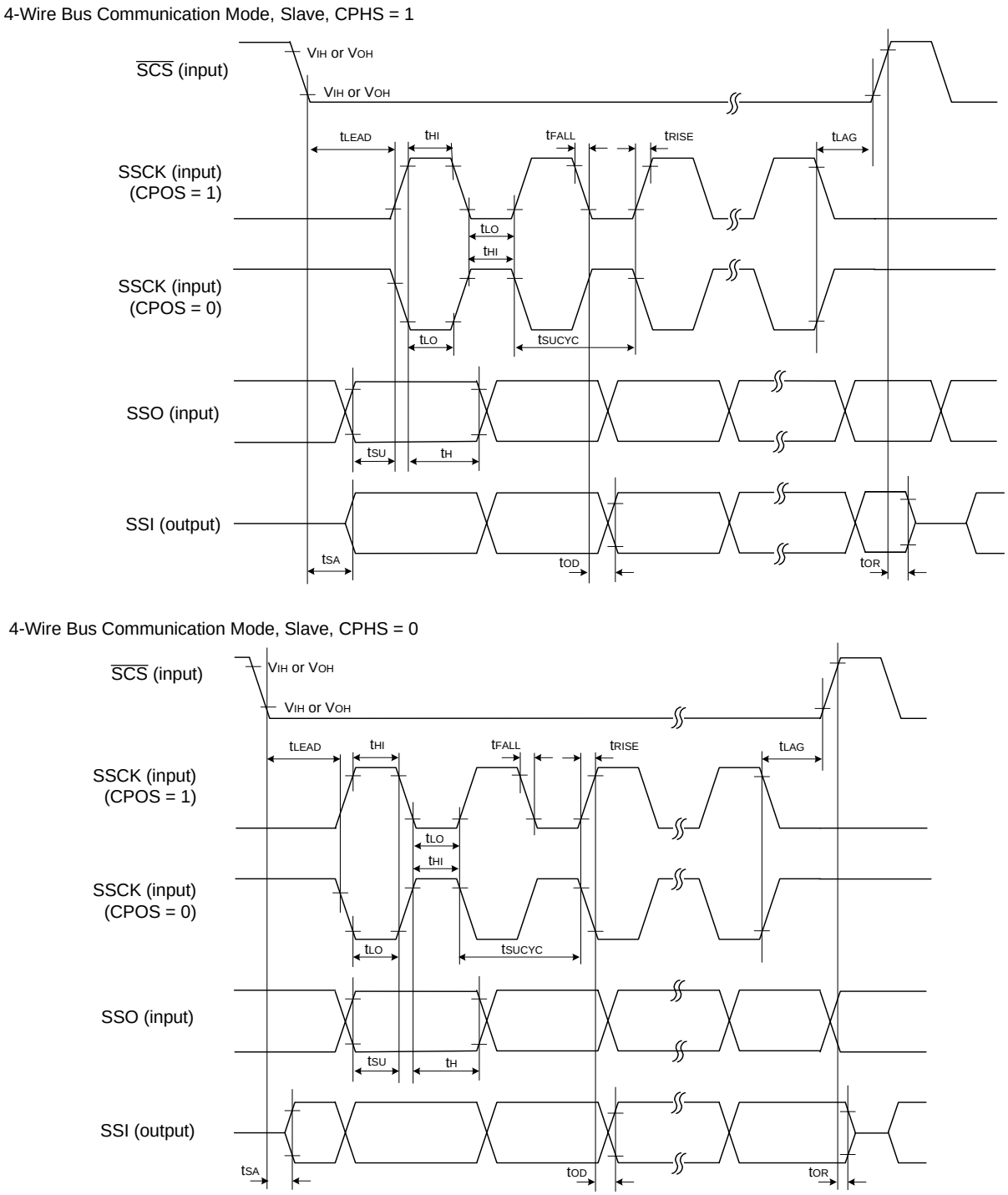


Figure 5.5 I/O Timing of Clock Synchronous Serial I/O with Chip Select (Slave)

Table 5.14 Electrical Characteristics (1) [V_{CC} = 5 V]

Symbol	Parameter		Condition		Standard			Unit
					Min.	Typ.	Max.	
V_{OH}	Output “H” voltage	Except X_{OUT}	I_{OH} = -5 mA		V_{CC} – 2.0	–	V_{CC}	V
			I_{OH} = -200 µA		V_{CC} – 0.3	–	V_{CC}	V
		X_{OUT}	Drive capacity HIGH	I_{OH} = -1 mA	V_{CC} – 2.0	–	V_{CC}	V
			Drive capacity LOW	I_{OH} = -500 µA	V_{CC} – 2.0	–	V_{CC}	V
V_{OL}	Output “L” voltage	Except P1_0 to P1_3, X_{OUT}	I_{OL} = 5 mA		–	–	2.0	V
			I_{OL} = 200 µA		–	–	0.45	V
		P1_0 to P1_3	Drive capacity HIGH	I_{OL} = 15 mA	–	–	2.0	V
			Drive capacity LOW	I_{OL} = 5 mA	–	–	2.0	V
			Drive capacity LOW	I_{OL} = 200 µA	–	–	0.45	V
		X_{OUT}	Drive capacity HIGH	I_{OL} = 1 mA	–	–	2.0	V
			Drive capacity LOW	I_{OL} = 500 µA	–	–	2.0	V
V_{T+}-V_{T-}	Hysteresis	$\overline{INT0}$, $\overline{INT1}$, $\overline{INT3}$, $\overline{KI0}$, $\overline{KI1}$, $\overline{KI2}$, $\overline{KI3}$, CNTR0, CNTR1, TCIN, RXD0			0.2	–	1.0	V
		$\overline{RESET}$			0.2	–	2.2	V
I_{IH}	Input “H” current		VI = 5 V		–	–	5.0	µA
I_{IL}	Input “L” current		VI = 0 V		–	–	-5.0	µA
R_{PULLUP}	Pull-up resistance		VI = 0 V		30	50	167	kΩ
R_{fXIN}	Feedback resistance	XIN			–	1.0	–	MΩ
f_{RING-S}	Low-speed on-chip oscillator frequency				40	125	250	kHz
V_{RAM}	RAM hold voltage		During stop mode		2.0	–	–	V

NOTE:
1. V_{CC} = 4.2 to 5.5 V at T_{opr} = -20 to 85 °C / -40 to 85 °C, f(XIN) = 20 MHz, unless otherwise specified.

Table 5.15 Electrical Characteristics (2) [Vcc = 5 V] (Topr = -40 to 85 °C, unless otherwise specified.)

Symbol	Parameter	Condition		Standard			Unit
				Min.	Typ.	Max.	
I_{CC}	Power supply current (V_{CC} = 3.3 to 5.5 V) Single-chip mode, output pins are open, other pins are V_{SS}, A/D converter is stopped	High-speed mode	XIN = 20 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz No division	–	9	15	mA
			XIN = 16 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz No division	–	8	14	mA
			XIN = 10 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz No division	–	5	–	mA
		Medium-speed mode	XIN = 20 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8	–	4	–	mA
			XIN = 16 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8	–	3	–	mA
			XIN = 10 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8	–	2	–	mA
		High-speed on-chip oscillator mode	Main clock off High-speed on-chip oscillator on = 8 MHz Low-speed on-chip oscillator on = 125 kHz No division	–	4	8	mA
			Main clock off High-speed on-chip oscillator on = 8 MHz Low-speed on-chip oscillator on = 125 kHz Divide-by-8	–	1.5	–	mA
		Low-speed on-chip oscillator mode	Main clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8 FMR47 = 1	–	110	300	µA
		Wait mode	Main clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz While a WAIT instruction is executed Peripheral clock operation VCA27 = VCA26 = 0	–	40	80	µA
		Wait mode	Main clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz While a WAIT instruction is executed Peripheral clock off VCA27 = VCA26 = 0	–	38	76	µA
		Stop mode	Main clock off, Topr = 25 °C High-speed on-chip oscillator off Low-speed on-chip oscillator off CM10 = 1 Peripheral clock off VCA27 = VCA26 = 0	–	0.8	3.0	µA

Table 5.22 Electrical Characteristics (4) [Vcc = 3 V] (Topr = -40 to 85 °C, unless otherwise specified.)

Symbol	Parameter	Condition		Standard			Unit
				Min.	Typ.	Max.	
I_{CC}	Power supply current (V_{CC} = 2.7 to 3.3 V) Single-chip mode, output pins are open, other pins are V_{SS}, A/D converter is stopped	High-speed mode	XIN = 20 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz No division	–	8	13	mA
			XIN = 16 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz No division	–	7	12	mA
			XIN = 10 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz No division	–	5	–	mA
		Medium-speed mode	XIN = 20 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8	–	3	–	mA
			XIN = 16 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8	–	2.5	–	mA
			XIN = 10 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8	–	1.6	–	mA
		High-speed on-chip oscillator mode	Main clock off High-speed on-chip oscillator on = 8 MHz Low-speed on-chip oscillator on = 125 kHz No division	–	3.5	7.5	mA
			Main clock off High-speed on-chip oscillator on = 8 MHz Low-speed on-chip oscillator on = 125 kHz Divide-by-8	–	1.5	–	mA
		Low-speed on-chip oscillator mode	Main clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8 FMR47 = 1	–	100	280	µA
		Wait mode	Main clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz While a WAIT instruction is executed Peripheral clock operation VCA27 = VCA26 = 0	–	37	74	µA
		Wait mode	Main clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz While a WAIT instruction is executed Peripheral clock off VCA27 = VCA26 = 0	–	35	70	µA
		Stop mode	Main clock off, Topr = 25 °C High-speed on-chip oscillator off Low-speed on-chip oscillator off CM10 = 1 Peripheral clock off VCA27 = VCA26 = 0	–	0.7	3.0	µA

Timing requirements (Unless Otherwise Specified: Vcc = 3 V, Vss = 0 V at Ta = 25 °C) [Vcc = 3 V]

Table 5.23 XIN Input

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(XIN)}$	XIN input cycle time	100	–	ns
$t_{WH(XIN)}$	XIN input “H” width	40	–	ns
$t_{WL(XIN)}$	XIN input “L” width	40	–	ns

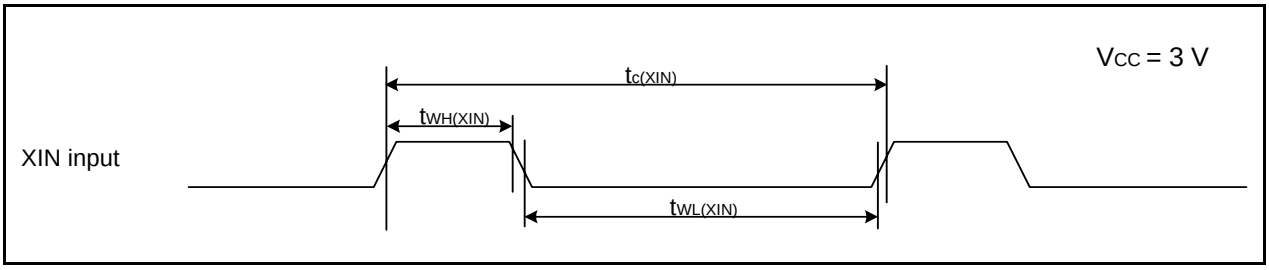


Figure 5.13 XIN Input Timing Diagram when Vcc = 3 V

Table 5.24 CNTR0 Input, CNTR1 Input, $\overline{\text{INT1}}$ Input

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(CNTR0)}$	CNTR0 input cycle time	300	–	ns
$t_{WH(CNTR0)}$	CNTR0 input “H” width	120	–	ns
$t_{WL(CNTR0)}$	CNTR0 input “L” width	120	–	ns

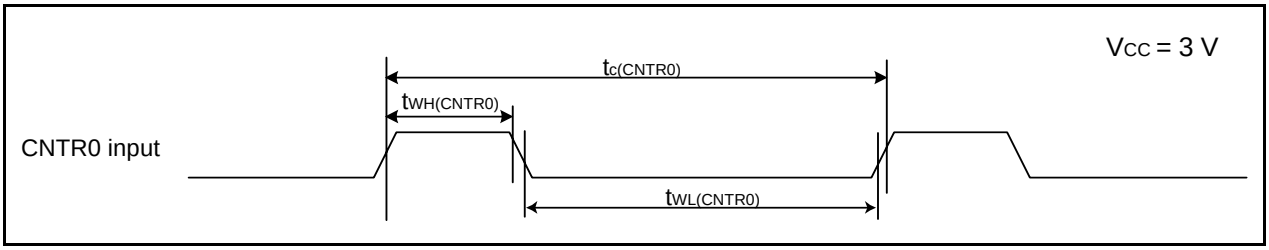


Figure 5.14 CNTR0 Input, CNTR1 Input, $\overline{\text{INT1}}$ Input Timing Diagram when Vcc = 3 V

Table 5.25 TCIN Input, $\overline{\text{INT3}}$ Input

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(TCIN)}$	TCIN input cycle time	1,200(1)	–	ns
$t_{WH(TCIN)}$	TCIN input “H” width	600(2)	–	ns
$t_{WL(TCIN)}$	TCIN input “L” width	600(2)	–	ns

NOTES:
1. When using the timer C input capture mode, adjust the cycle time to (1/timer C count source frequency x 3) or above.
2. When using the timer C input capture mode, adjust the width to (1/timer C count source frequency x 1.5) or above.

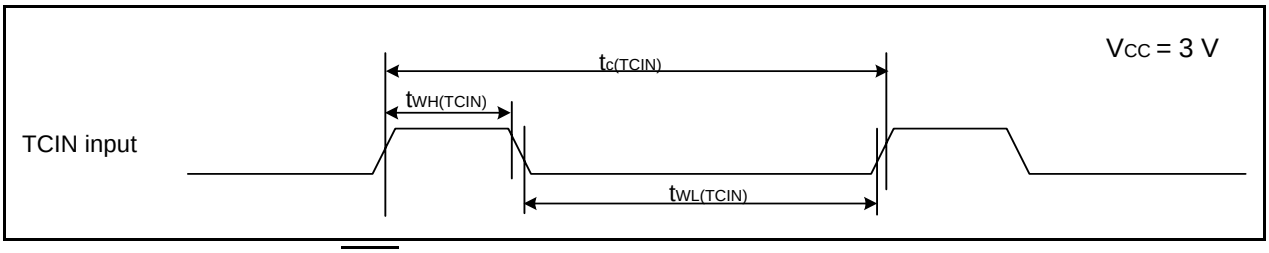


Figure 5.15 TCIN Input, $\overline{\text{INT3}}$ Input Timing Diagram when Vcc = 3 V

Table 5.26 Serial Interface

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(CK)}$	CLKi input cycle time	300	–	ns
$t_{W(CKH)}$	CLKi input “H” width	150	–	ns
$t_{W(CKL)}$	CLKi input “L” width	150	–	ns
$t_{d(C-Q)}$	TXDi output delay time	–	80	ns
$t_{h(C-Q)}$	TXDi hold time	0	–	ns
$t_{su(D-C)}$	RXDi input setup time	70	–	ns
$t_{h(C-D)}$	RXDi input hold time	90	–	ns

i = 0 or 1

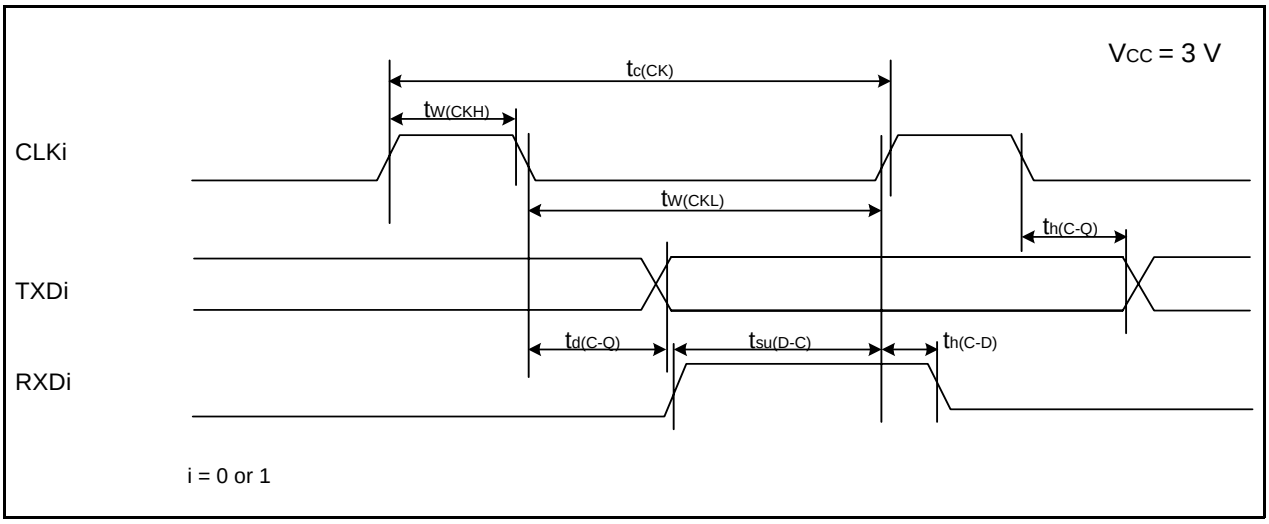


Figure 5.16 Serial Interface Timing Diagram when VCC = 3 V

Table 5.27 External Interrupt $\overline{INT0}$ Input

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{W(INH)}$	$\overline{INT0}$ input “H” width	380(1)	–	ns
$t_{W(INL)}$	$\overline{INT0}$ input “L” width	380(2)	–	ns

NOTES:
1. When selecting the digital filter by the $\overline{INT0}$ input filter select bit, use an $\overline{INT0}$ input HIGH width of either (1/digital filter clock frequency x 3) or the minimum value of standard, whichever is greater
2. When selecting the digital filter by the $\overline{INT0}$ input filter select bit, use an $\overline{INT0}$ input LOW width of either (1/digital filter clock frequency x 3) or the minimum value of standard, whichever is greater

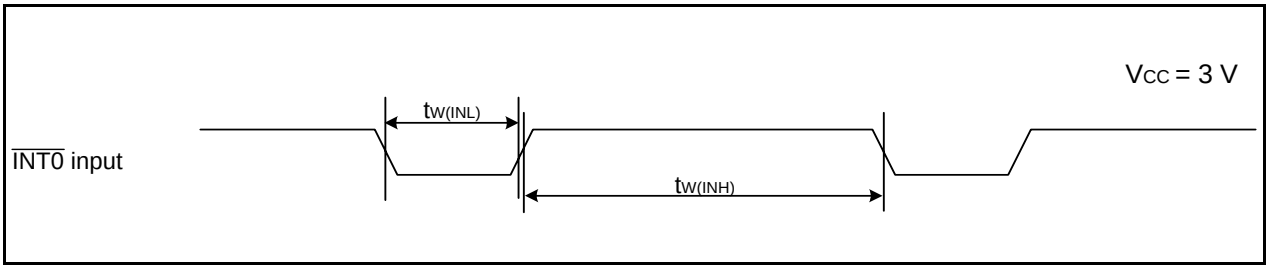


Figure 5.17 External Interrupt $\overline{INT0}$ Input Timing Diagram when VCC = 3 V

REVISION HISTORY	R8C/1A Group, R8C/1B Group Datasheet

Rev.	Date	Description	
		Page	Summary
1.00	Sep 01, 2005	18	Table 4.3 SFR Information(3); 0085h: "Prescaler Z" → "Prescaler Z Register" 0086h: "Timer Z Secondary" → "Timer Z Secondary Register" 0087h: "Timer Z Primary" → "Timer Z Primary Register" 008Ch: "Prescaler X" → "Prescaler X Register" 008Dh: "Timer X" → "Timer X Register" 0090h, 0091h: "Timer C" → "Timer C Register" revised
		21	Table 5.3 A/D Converter Characteristics; V_{ref} and V_{IA}: Standard value, NOTE4 revised
		22	Table 5.4 Flash Memory (Program ROM) Electrical Characteristics; NOTES3 and 5 revised, NOTE8 deleted
		23	Table 5.5 Flash Memory (Data flash Block A, Block B) Electrical Characteristics; NOTES1 and 3 revised
		25	Table 5.8 Reset Circuit Electrical Characteristics (When Using Voltage Monitor 1 Reset); NOTE2 revised
		26	Table 5.10 High-speed On-Chip Oscillator Circuit Electrical Characteristics; "High-Speed On-Chip Oscillator ..." → "High-Speed On-Chip Oscillator Frequency ..." revised, NOTE2 added
		33	Table 5.15 Electrical Characteristics (2) [Vcc = 5V]; NOTE1 deleted
		37	Table 5.22 Electrical Characteristics (4) [Vcc = 3V]; NOTE1 deleted
1.10	Dec 16, 2005	–	Products of PWQN0028KA-B package included
		5, 6	Table 1.3, Table 1.4 revised
		24	Table 5.4 Flash Memory (Program ROM) Electrical Characteristics; NOTE 8 added, Topr → Ambient temperature
		25	Table 5.5 Flash Memory (Data flash Block A, Block B) Electrical Characteristics; NOTE 9 added, Topr → Ambient temperature
		28	Table 5.10 High-speed On-Chip Oscillator Circuit Electrical Characteristics; NOTE 3 added
		29	Table 5.12; tSA and tOR revised, NOTE: 1. VCC = 2.2 to → 2.7 to
		33	Table 5.13; NOTE: 1. VCC = 2.2 to → 2.7 to
		35, 39	Table 5.15, Table 5.22; The title revised, Condition of Stop Mode added
		37, 41	Table 5.19, Table 5.26; td(C-Q) and tsu(D-C) revised
		42, 43	Package Dimensions revised
1.20	Mar 31, 2006	5, 6	Table 1.3, Table 1.4; Type No. added, deleted
		16, 17	Figure 3.1, Figure 3.2; Part Number added, deleted
		24, 25	Table 5.4, Table 5.5; Conditions: VCC = 5.0 V at Topr = 25 °C deleted,
1.30	Oct 03, 2006	all pages	Y version added Factory programming product added

REVISION HISTORY	R8C/1A Group, R8C/1B Group Datasheet

Rev.	Date	Description	
		Page	Summary
1.30	Oct 03, 2006	1	1.1 “portable equipment” added
		2, 3	Table 1.1, Table 1.2; Specification Interrupts: “Internal: 9 sources” → “Internal: 11 sources”
		24	Table 5.2; Parameter: System clock added
		45	Package Dimensions; PWQN0028KA-B revised
1.40	Dec 08, 2006	20	Table 4.1; 000Fh: After reset “000XXXXXb” → “00X11111b”
		24	Table 19.2; Parameter: OCD2 = 1 On-chip oscillator clock selected revised